

PSMN2R0-60ES

N-channel 60 V 2.2 mΩ standard level MOSFET in I2PAK

Rev. 02 — 19 April 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

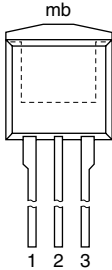
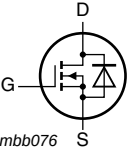
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see Figure 1	[1] -	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	338	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see Figure 12	[2] -	1.8	2.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see Figure 12 ; see Figure 13	-	3	3.5	mΩ
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 75 A;	-	32	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; see Figure 14 ; see Figure 15	-	137	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 120 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; Unclamped	-	-	913	mJ



[1] Continuous current limited by package.
[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT226 (I2PAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R0-60ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

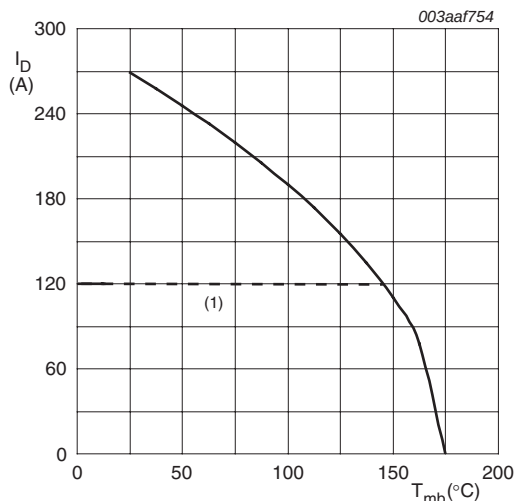
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

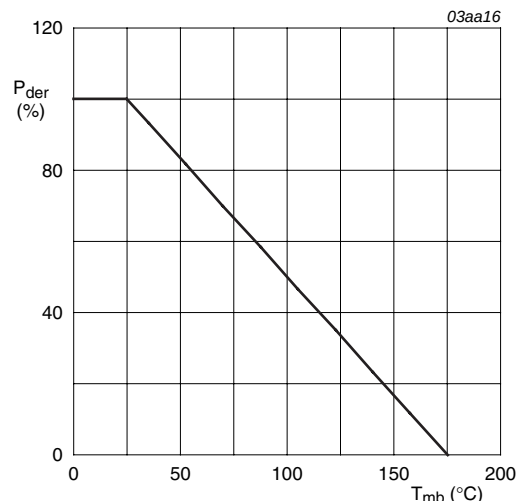
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	60	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	[1]	120	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	[1]	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 3	-	1135	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	338	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{slid(M)}$	peak soldering temperature		-	260	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	1135	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 120\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 50\text{ }\Omega$; Unclamped	-	913	mJ

[1] Continuous current limited by package



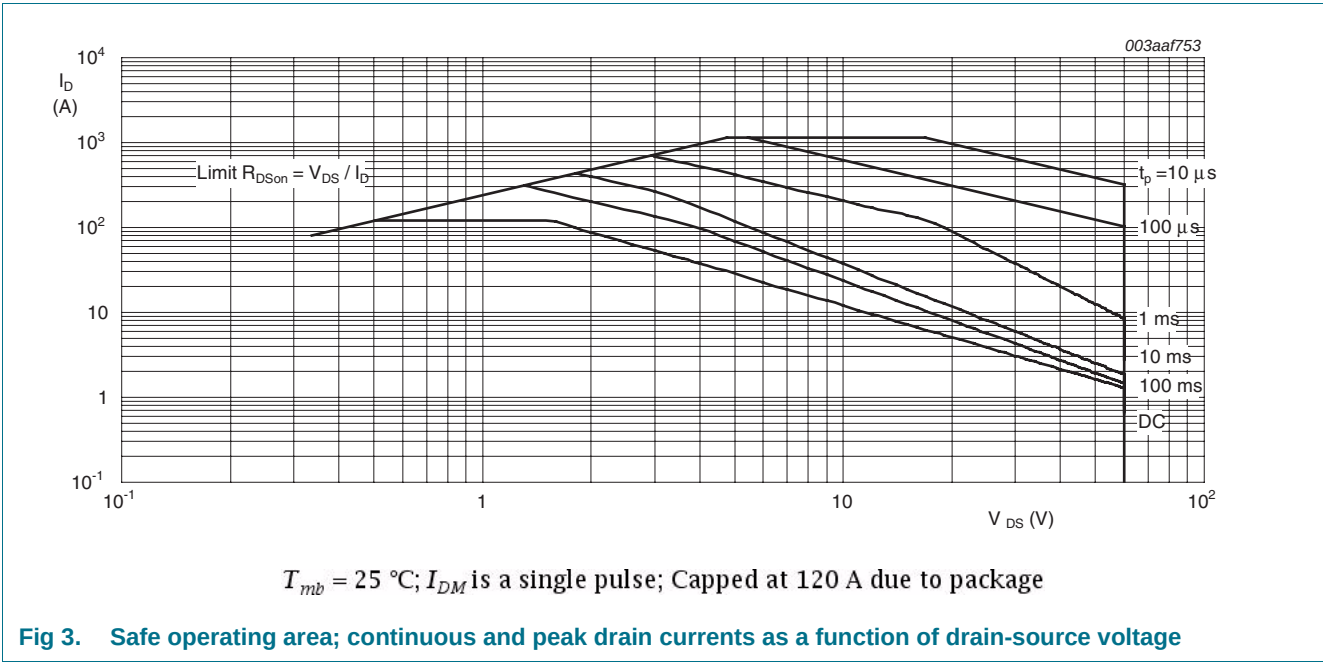
$V_{GS} \geq 10\text{ V}$ (1) Capped at 120 A due to package

Fig 1. Continuous drain current as a function of mounting base temperature.



$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

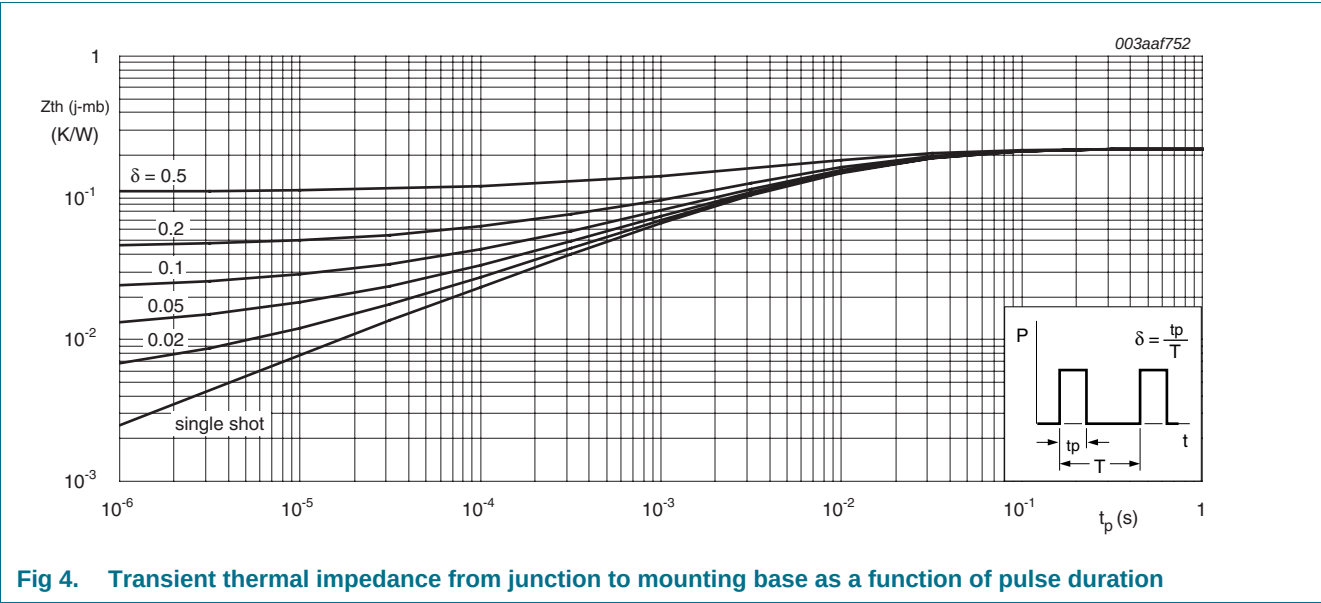
Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



6. Characteristics

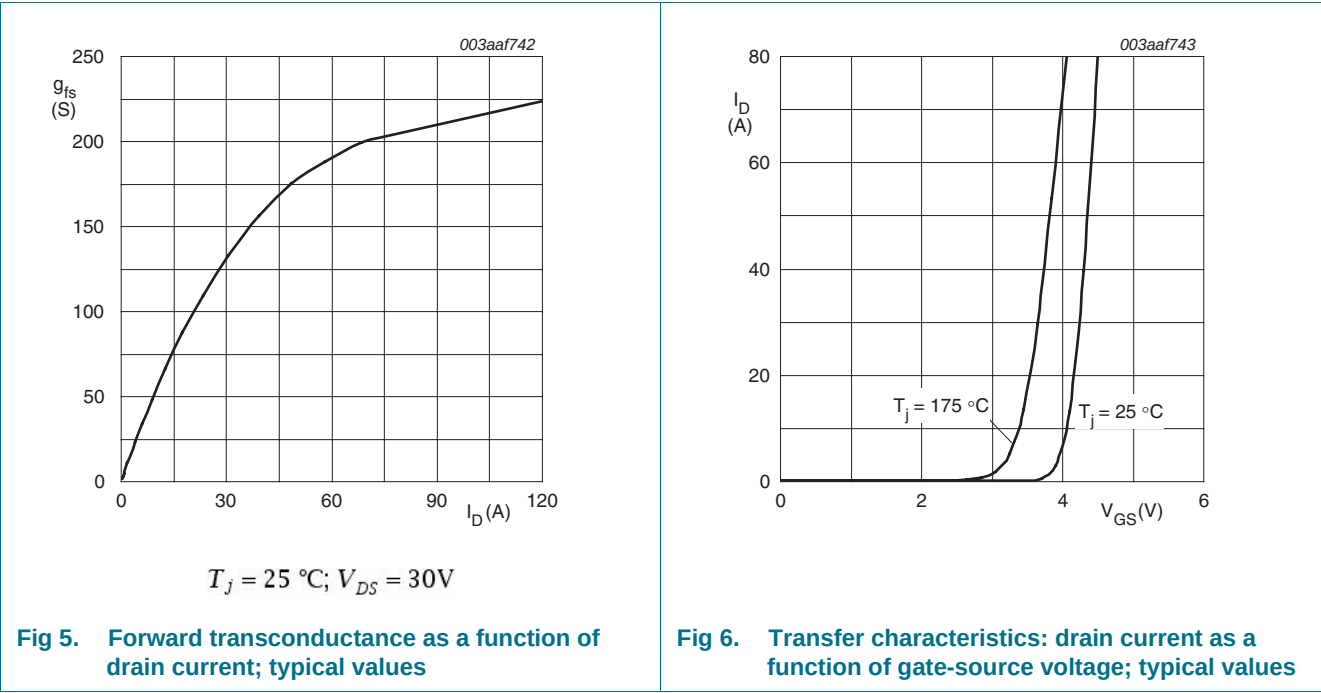
Table 6. Characteristics

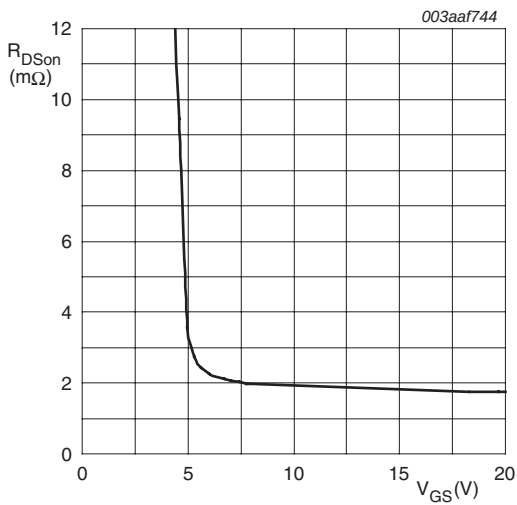
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_j = -55\ ^\circ\text{C}$	54	-	-	V
		$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_j = -55\ ^\circ\text{C}$; see Figure 10	-	-	4.6	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_j = 175\ ^\circ\text{C}$; see Figure 10	1	-	-	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ\text{C}$; see Figure 11 ; see Figure 10	2	3	4	V
I_{DSS}	drain leakage current	$V_{DS} = 60\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	-	0.03	10	μA
		$V_{DS} = 60\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_j = 175\ ^\circ\text{C}$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = -20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	-	-	100	nA
		$V_{GS} = 20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_j = 25\ ^\circ\text{C}$; see Figure 12	^[1] -	1.8	2.2	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_j = 175\ ^\circ\text{C}$; see Figure 12 ; see Figure 13	-	4.3	5.1	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_j = 100\ ^\circ\text{C}$; see Figure 12 ; see Figure 13	-	3	3.5	mΩ
R_G	gate resistance	$f = 1\ \text{MHz}$	-	0.9	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 75\ \text{A}$; $V_{DS} = 30\ \text{V}$; $V_{GS} = 10\ \text{V}$; see Figure 14 ; see Figure 15	-	137	-	nC
		$I_D = 0\ \text{A}$; $V_{DS} = 0\ \text{V}$; $V_{GS} = 10\ \text{V}$; see Figure 14 ; see Figure 15	-	129	-	nC
Q_{GS}	gate-source charge	$I_D = 75\ \text{A}$; $V_{DS} = 30\ \text{V}$; $V_{GS} = 10\ \text{V}$	-	48	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 75\ \text{A}$; $V_{DS} = 30\ \text{V}$; $V_{GS} = 10\ \text{V}$; see Figure 14 ; see Figure 15	-	29	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	19	-	nC
Q_{GD}	gate-drain charge		-	32	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30\ \text{V}$; see Figure 14 ; see Figure 15	-	5.7	-	V
C_{iss}	input capacitance	$V_{DS} = 30\ \text{V}$; $V_{GS} = 0\ \text{V}$; $f = 1\ \text{MHz}$; $T_j = 25\ ^\circ\text{C}$; see Figure 16	-	9997	-	pF
C_{oss}	output capacitance		-	1210	-	pF
C_{rss}	reverse transfer capacitance		-	594	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\ \text{V}$; $R_L = 0.4\ \Omega$; $V_{GS} = 10\ \text{V}$; $R_{G(ext)} = 4.7\ \Omega$; $I_D = 75\ \text{A}$	-	42	-	ns
t_r	rise time		-	56	-	ns
$t_{d(off)}$	turn-off delay time		-	115	-	ns
t_f	fall time		-	49	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; see Figure 17	-	0.8	1.2	V
t_{rr}	reverse recovery time	$I_S = 25\text{ A}$; $dI_S/dt = -100\text{ A/}\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 30\text{ V}$	-	57	-	ns
Q_r	recovered charge	$I_S = 25\text{ A}$; $dI_S/dt = -100\text{ A/}\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 30\text{ V}$	-	80	-	nC

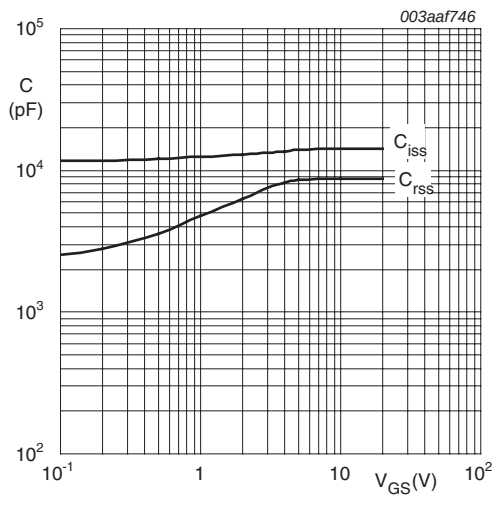
[1] Measured 3 mm from package.





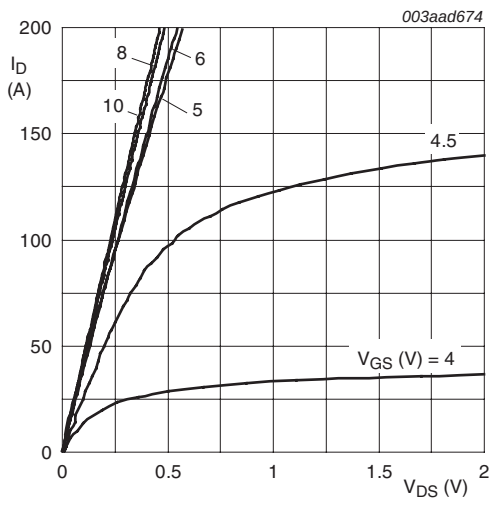
$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



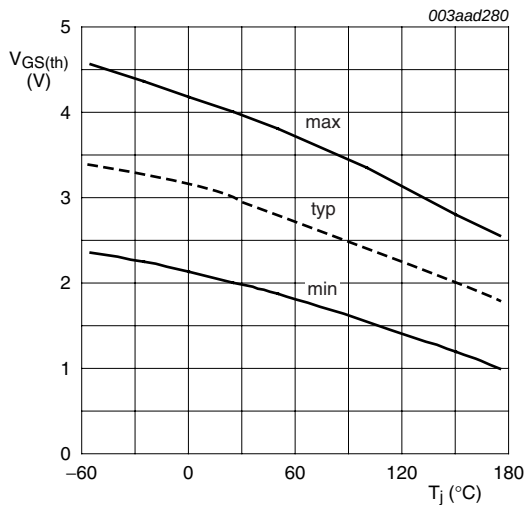
$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values



$T_j = 25\text{ }^{\circ}\text{C}; t_p = 300\mu\text{s}$

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

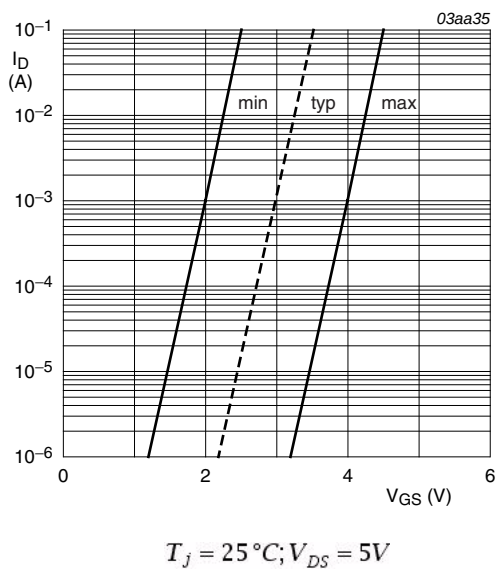


Fig 11. Sub-threshold drain current as a function of gate-source voltage

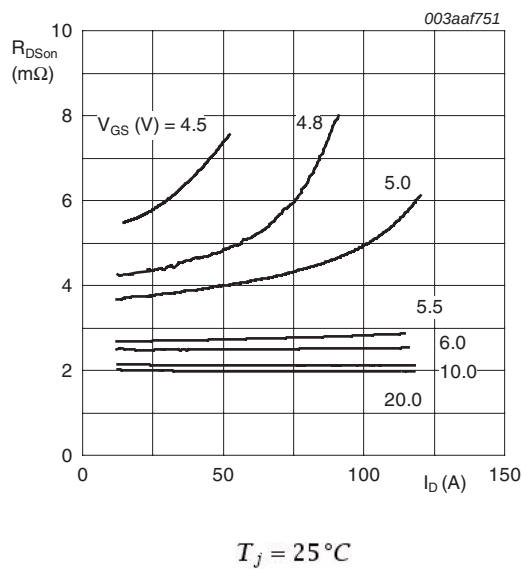


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

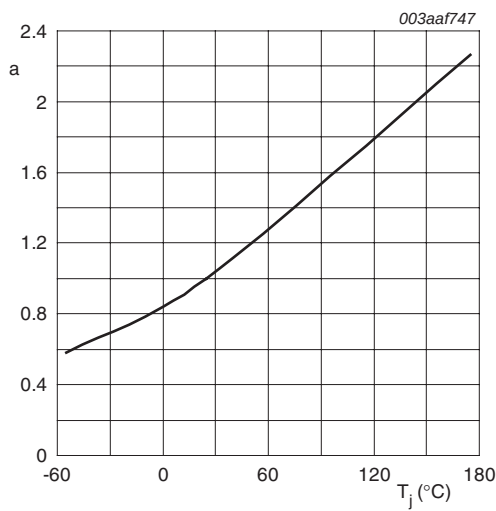


Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

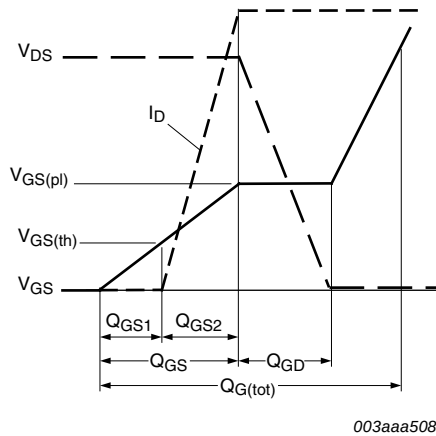
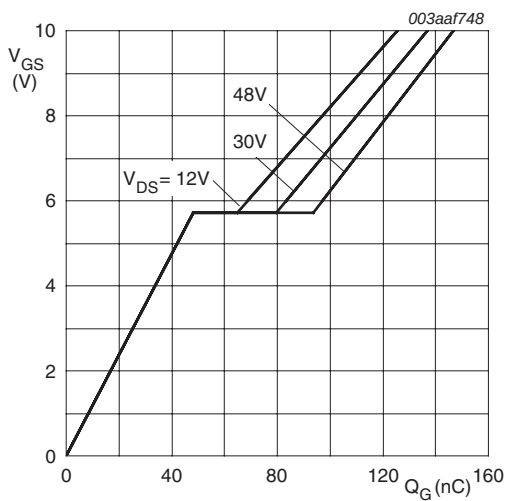
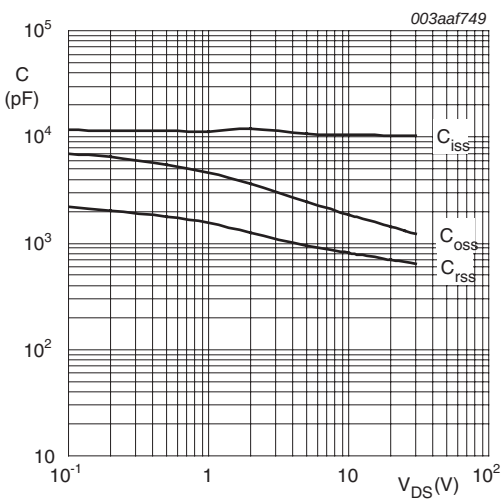


Fig 14. Gate charge waveform definitions



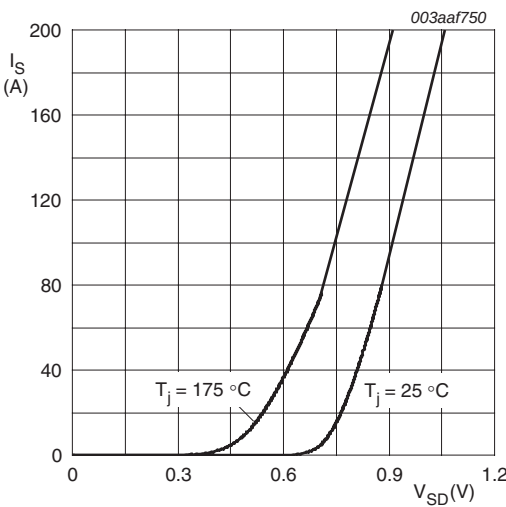
$T_J = 25\text{ }^{\circ}\text{C}; I_D = 75\text{ A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226

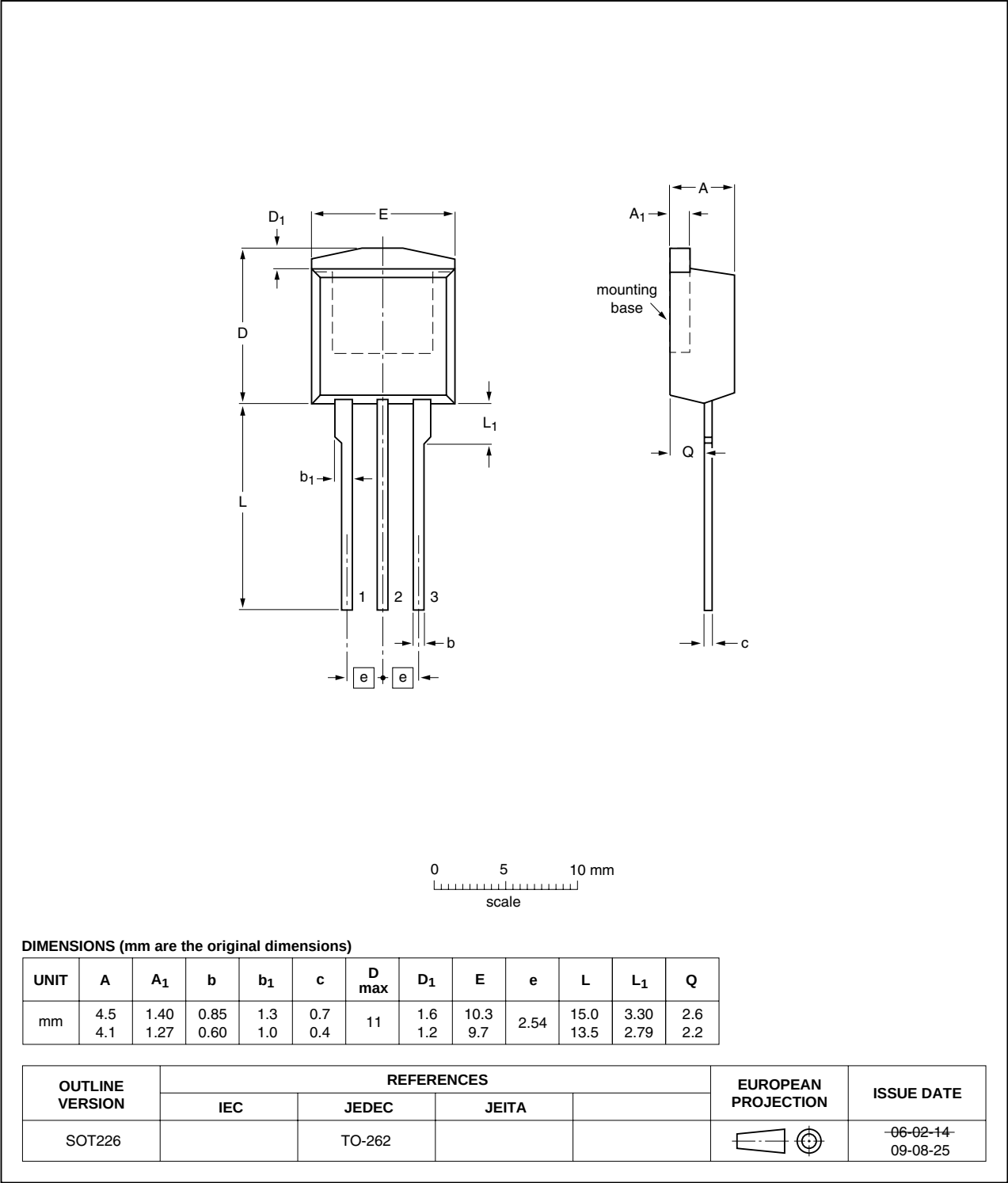


Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R0-60ES v.2	20110419	Product data sheet	-	PSMN2R0-60ES v.1
Modifications:	• Status changed from objective to product. • Various changes to content.			
PSMN2R0-60ES v.1	20110117	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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